

PSMN9R5-100BS

N-channel 100 V 9.6 m Ω standard level MOSFET in D2PAK Rev. 2 — 2 March 2012 Product data s

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	-	89	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	211	W
Tj	junction temperature		-55	-	175	°C
Static charac	teristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	8.16	9.6	mΩ
Dynamic cha	racteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 60 \text{ A}; V_{DS} = 50 \text{ V};$	-	23	-	nC
Q _{G(tot)}	total gate charge	see Figure 14;see Figure 15	-	82	-	nC
Avalanche ru	iggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 89 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω	-	-	177	mJ



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN9R5-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	63	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	-	89	Α
I_{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3	-	355	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	211	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	-	89	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	355	Α
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 89 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω	-	177	mJ

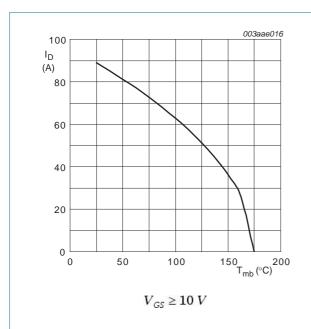


Fig 1. Continuous drain current as a function of mounting base temperature

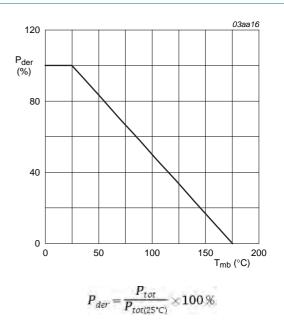
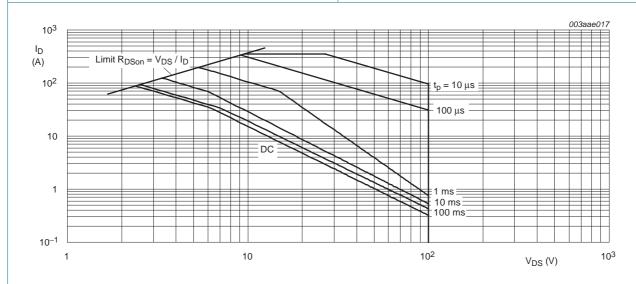


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25 \,^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 4</u>	-	0.38	0.71	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

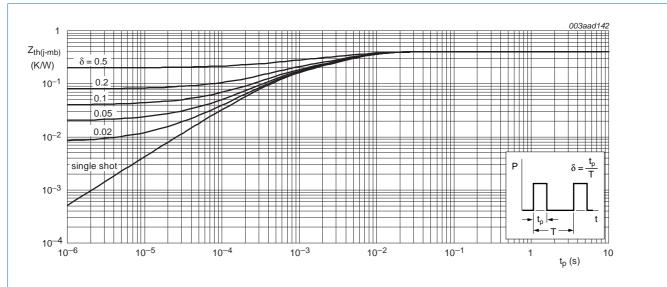


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see Figure 10; see Figure 11	-	-	4.8	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	100	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	4	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	-	17.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	23.5	27.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	8.16	9.6	mΩ
R _G	internal gate resistance	f = 1 MHz	-	0.7	-	Ω
	(AC)					
Dynamic ((AC)					
		$I_D = 0 \text{ A}$; $V_{DS} = 0 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14	-	67	-	nC
	characteristics		-	67 82	-	nC nC
Q _{G(tot)}	characteristics	see Figure 14				
$Q_{G(tot)}$	characteristics total gate charge	see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$;	-	82	-	nC
$Q_{G(tot)}$ Q_{GS} $Q_{GS(th)}$	total gate charge gate-source charge pre-threshold	see Figure 14 $I_D = 60 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15 $I_D = 60 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 3 \text{ V};$	-	82 21	-	nC nC
$Q_{G(tot)}$ Q_{GS} $Q_{GS(th)}$ $Q_{GS(th-pl)}$	characteristics total gate charge gate-source charge pre-threshold gate-source charge post-threshold	see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 3 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$;	- - -	82 21 13.1	-	nC nC
Q _G (tot) Q _{GS} Q _{GS(th)} Q _{GS(th-pl)}	characteristics total gate charge gate-source charge pre-threshold gate-source charge post-threshold gate-source charge	see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 3 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14	- - -	82 21 13.1 7.8		nC nC nC
Q _G (tot) Q _{GS} Q _{GS(th)} Q _{GS(th-pl)} Q _{GD}	characteristics total gate charge gate-source charge pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau	see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 3 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $V_{DS} = 50 \text{ V}$; see Figure 14;	- - -	82 21 13.1 7.8		nC nC nC
$Q_{G(tot)}$ Q_{GS} $Q_{GS(th)}$ $Q_{GS(th-pl)}$ Q_{GD} $Q_{GS(pl)}$ $Q_{GS(pl)}$	characteristics total gate charge gate-source charge pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage	see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 3 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $V_{DS} = 50 \text{ V}$; see Figure 14; see Figure 15	- - -	82 21 13.1 7.8 23 4.5		nC nC nC
QG(tot) QGS QGS(th) QGS(th-pl) QGD VGS(pl) Ciss Coss	characteristics total gate charge gate-source charge pre-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-source plateau voltage input capacitance	see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 3 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $V_{DS} = 50 \text{ V}$; see Figure 14; see Figure 15 $V_{DS} = 50 \text{ V}$; $V_{GS} = 0 \text{ V}$; $V_{GS} = 10 \text{ MHz}$;	- - -	82 21 13.1 7.8 23 4.5		nC nC nC nC
QG(tot) QGS QGS(th) QGS(th-pl) QGD VGS(pl) Ciss Coss Crss	gate-source charge pre-threshold gate-source charge post-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-drain charge input capacitance output capacitance reverse transfer	see Figure 14 $I_D = 60 \text{ A; } V_{DS} = 50 \text{ V; } V_{GS} = 10 \text{ V; }$ $see Figure 14; see Figure 15$ $I_D = 60 \text{ A; } V_{DS} = 50 \text{ V; } V_{GS} = 3 \text{ V; }$ $see Figure 14$ $I_D = 60 \text{ A; } V_{DS} = 50 \text{ V; } V_{GS} = 10 \text{ V; }$ $see Figure 14$ $I_D = 60 \text{ A; } V_{DS} = 50 \text{ V; } V_{GS} = 10 \text{ V; }$ $see Figure 14; see Figure 15$ $V_{DS} = 50 \text{ V; } see Figure 14; $ $see Figure 15$ $V_{DS} = 50 \text{ V; } V_{GS} = 0 \text{ V; } f = 1 \text{ MHz; }$ $T_j = 25 \text{ °C; } see Figure 16$	- - - - -	82 21 13.1 7.8 23 4.5 4454 302	- - - -	nC nC nC nC
QG(tot) QGS QGS(th) QGS(th-pl) QGD VGS(pl) Ciss Coss Crss	gate-source charge pre-threshold gate-source charge post-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-drain charge input capacitance output capacitance reverse transfer capacitance	see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 3 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14 $I_D = 60 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15 $V_{DS} = 50 \text{ V}$; see Figure 14; see Figure 15 $V_{DS} = 50 \text{ V}$; $V_{GS} = 0 \text{ V}$; $V_{GS} = 10 \text{ MHz}$;	- - - - -	82 21 13.1 7.8 23 4.5 4454 302 185	- - - - -	nC nC nC nC v
Dynamic (QGS QGS(th) QGS(th-pl) QGD VGS(pl) Ciss Coss Crss td(on) tr	gate-source charge pre-threshold gate-source charge post-threshold gate-source charge post-threshold gate-source charge gate-drain charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time	see Figure 14 $I_D = 60 \text{ A; } V_{DS} = 50 \text{ V; } V_{GS} = 10 \text{ V; }$ $see Figure 14; see Figure 15$ $I_D = 60 \text{ A; } V_{DS} = 50 \text{ V; } V_{GS} = 3 \text{ V; }$ $see Figure 14$ $I_D = 60 \text{ A; } V_{DS} = 50 \text{ V; } V_{GS} = 10 \text{ V; }$ $see Figure 14$ $I_D = 60 \text{ A; } V_{DS} = 50 \text{ V; } V_{GS} = 10 \text{ V; }$ $see Figure 14; see Figure 15$ $V_{DS} = 50 \text{ V; } see Figure 14; $ $see Figure 15$ $V_{DS} = 50 \text{ V; } V_{GS} = 0 \text{ V; } f = 1 \text{ MHz; }$ $T_j = 25 \text{ °C; } see Figure 16$ $V_{DS} = 50 \text{ V; } R_L = 0.8 \text{ Ω; } V_{GS} = 10 \text{ V; }$	- - - - -	82 21 13.1 7.8 23 4.5 4454 302 185	- - - - -	nC nC nC v pF pF pF ns

PSMN9R5-100BS

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 C_{iss}

 C_{rss}

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
V _{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 17</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	61.5	-	ns
Qr	recovered charge	$V_{DS} = 50 \text{ V}$	-	157	-	nC

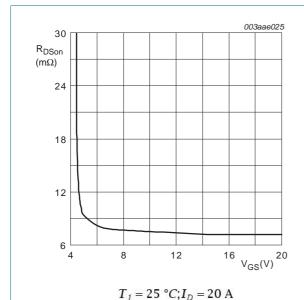


Fig 5. Drain-source on-state resistance as a function of gate-source voltage; typical values

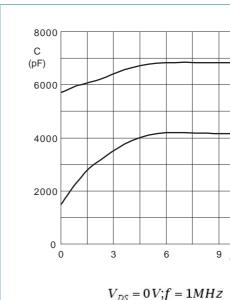


Fig 6. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

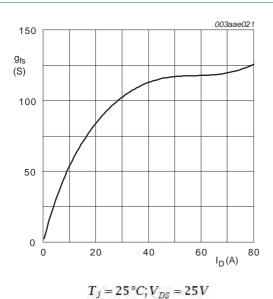


Fig 7. Forward transconductance as a function of drain current; typical values

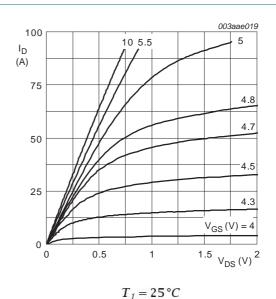


Fig 8. Output characteristics: drain current as a function of drain-source voltage; typical values

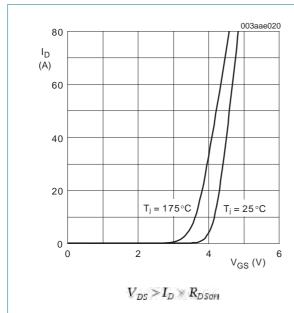


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

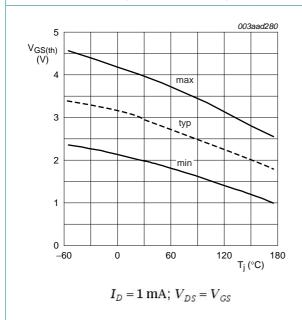
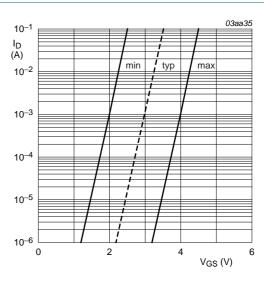


Fig 11. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

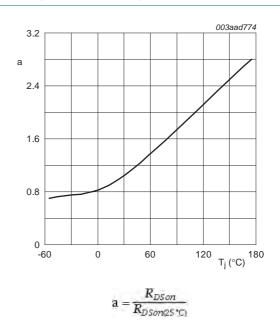


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

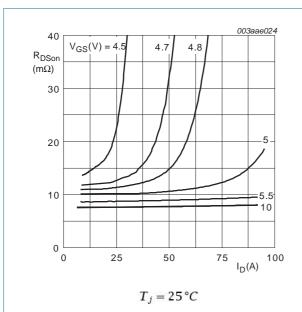


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

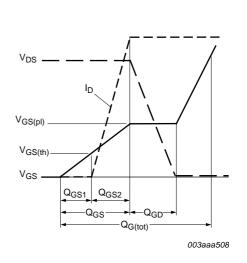


Fig 14. Gate charge waveform definitions

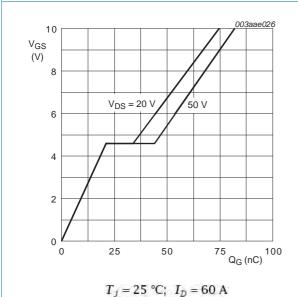
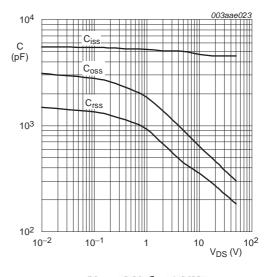
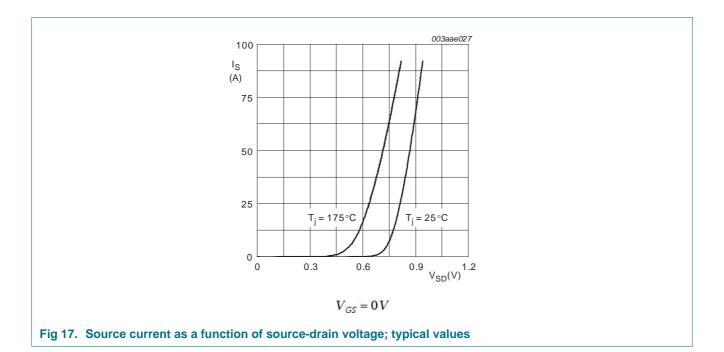


Fig 15. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

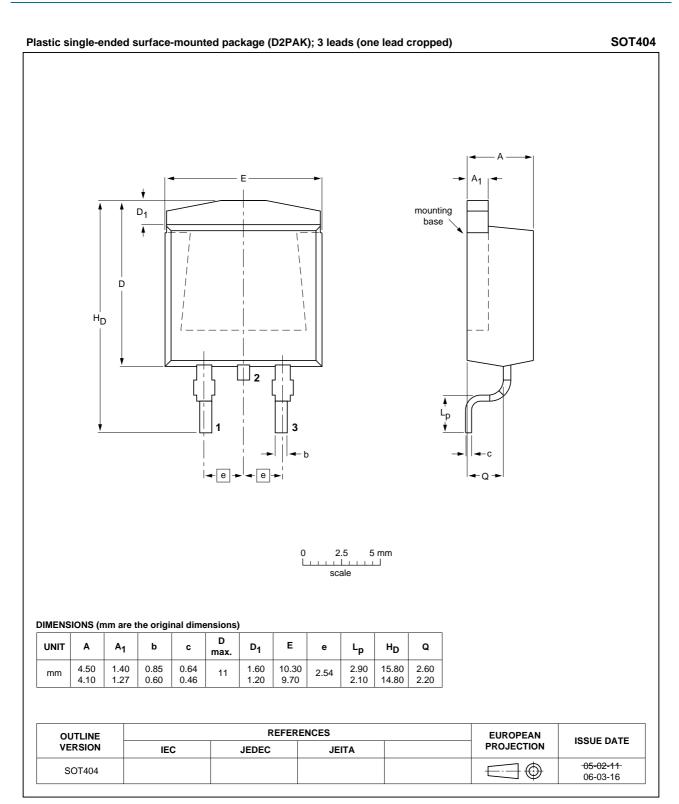


Fig 18. Package outline SOT404 (D2PAK)

Revision history

Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN9R5-100BS v.2	20120302	Product data sheet	-	PSMN9R5-100BS v.1
Modifications:	· ·	om objective to product.		
	 Various changes to 	o content.		
PSMN9R5-100BS v.1	20111025	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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PSMN9R5-100BS

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PSMN9R5-100BS

N-channel 100 V 9.6 mΩ standard level MOSFET in D2PAK

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